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Understanding the Initial Stages of TDDB in Si/SiO2 MOSFETS Utilizing EDMR and NZFMR

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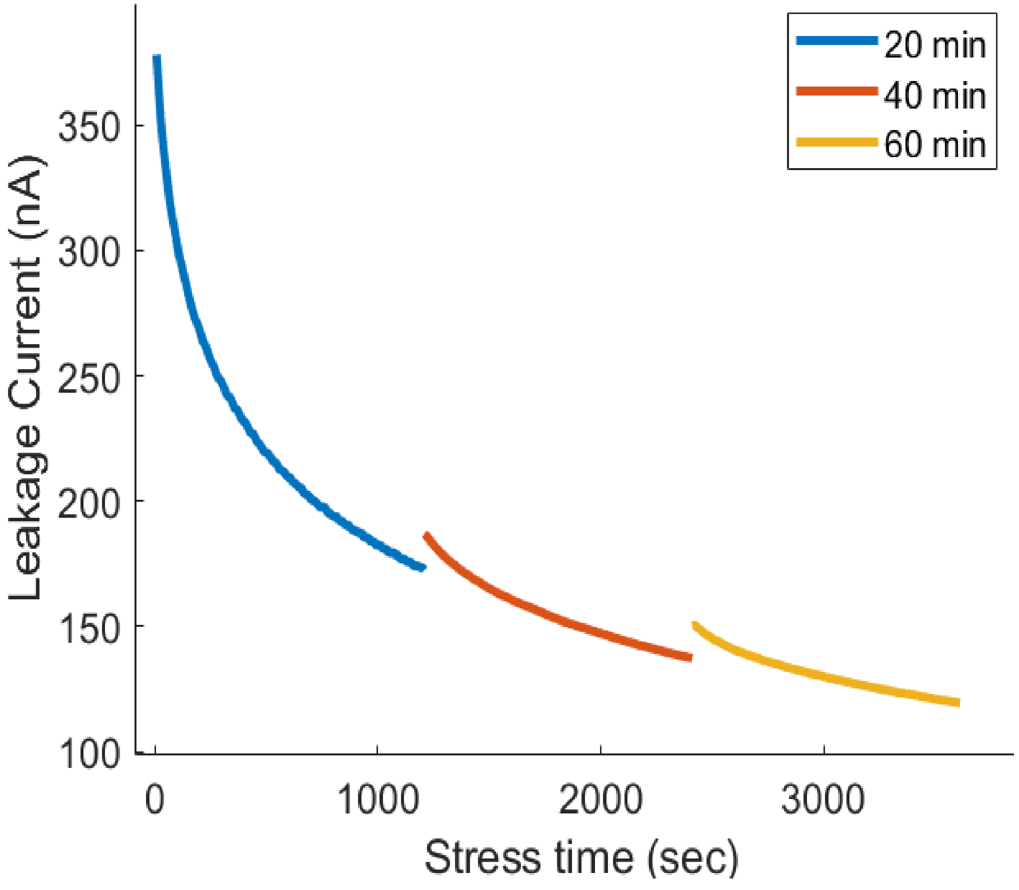
Goals of Study

- Investigate leakage currents in Si/SiO_2 MOSFETs due to TDDB with EDMR via SDTAT.
- Analyze interface damage via dc I-V SDR/EDMR to develop an understanding of the initial stages of TDDB.
- Explore the kinetics of SDTAT and chemical changes at the interface throughout high-field stressing via NZFMR.

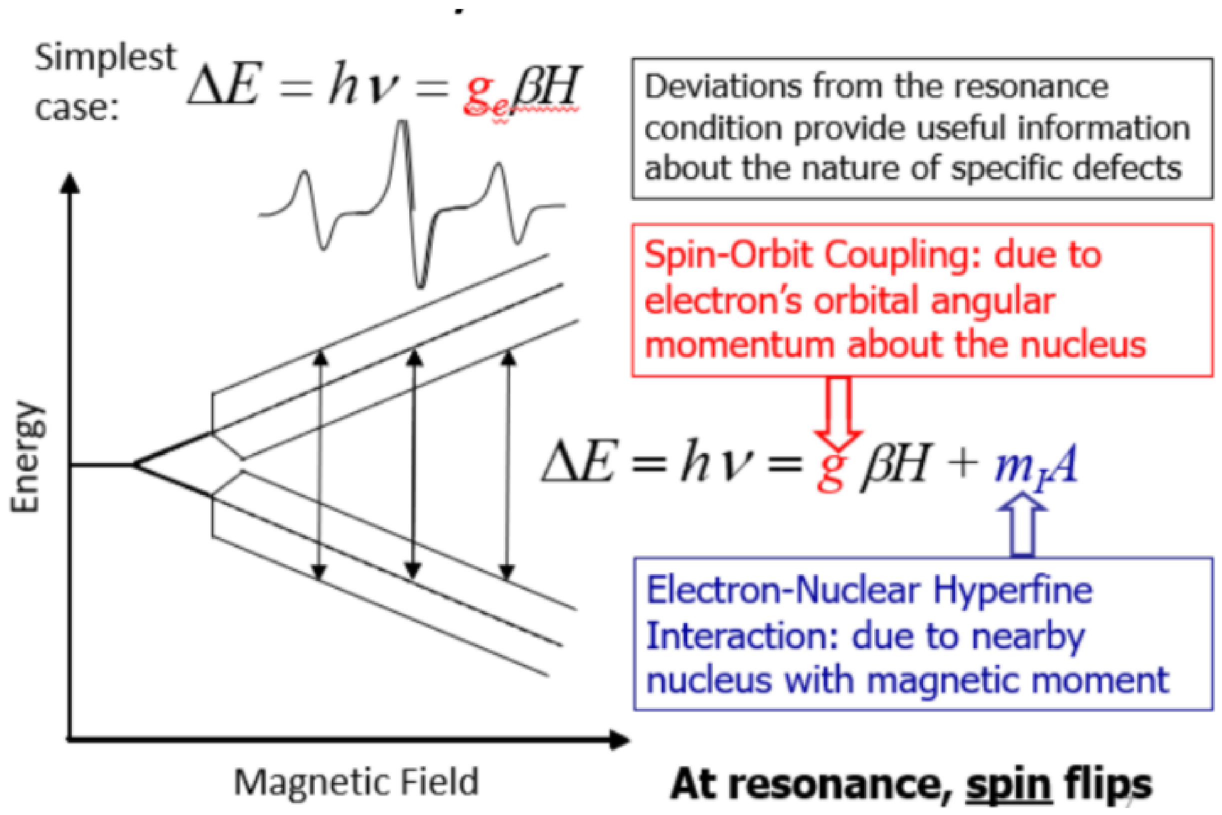
Time Dependent Dielectric Breakdown (TDDB)

- TDDB is one of the most important reliability problems in solid-state electronics.
- Device structures can be aged through high constant voltage stressing.
- This stressing results in a change in both the stress-induced leakage current (SILC) and changes in Fowler-Nordheim tunneling.



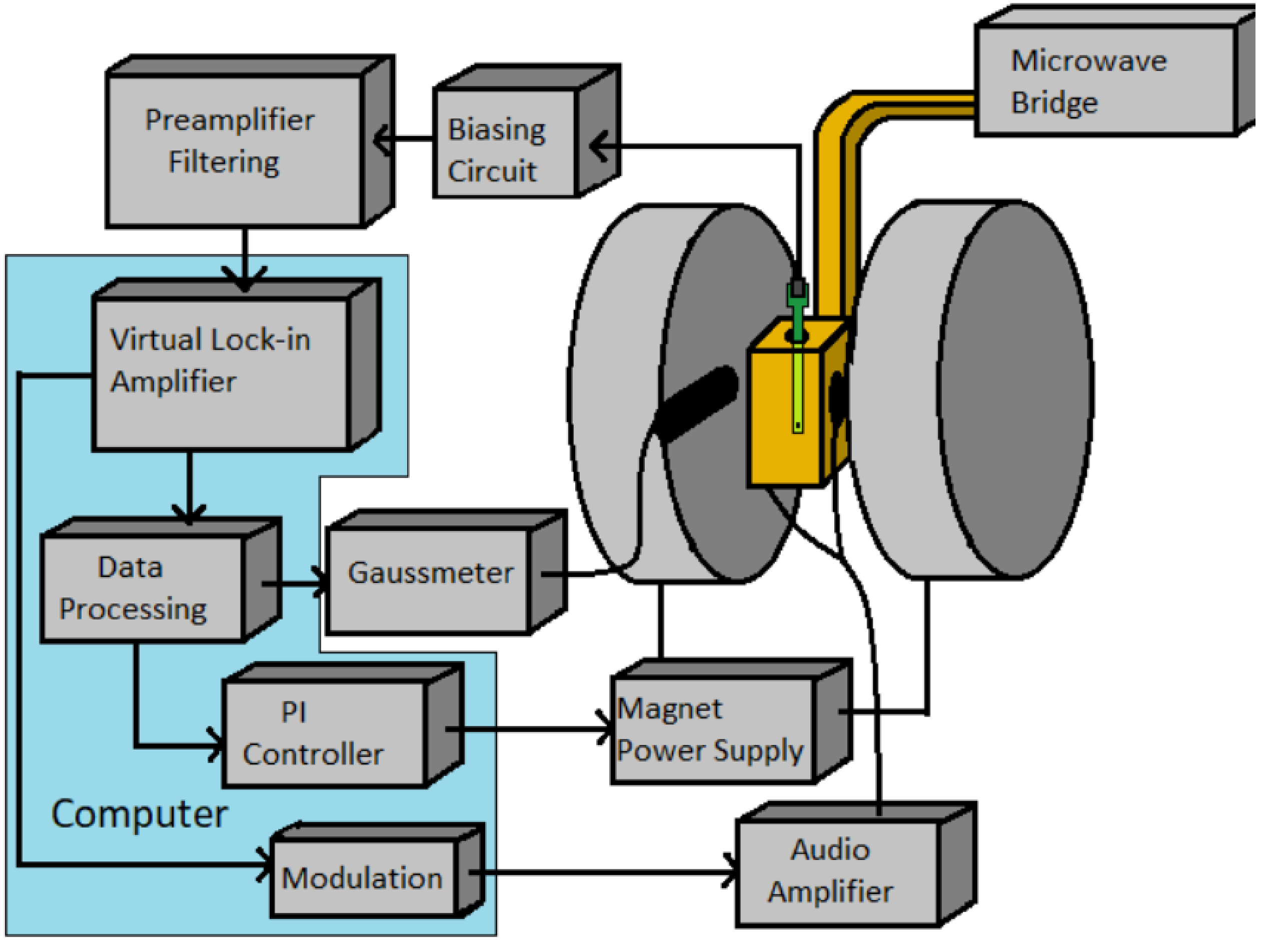
Overview of Magnetic Resonance

- Energy levels of paramagnetic defect sites are split by a magnetic field.
- By applying a microwave radiation of frequency v and a slowly-changing H to a sample, one can "flip" defect electrons.



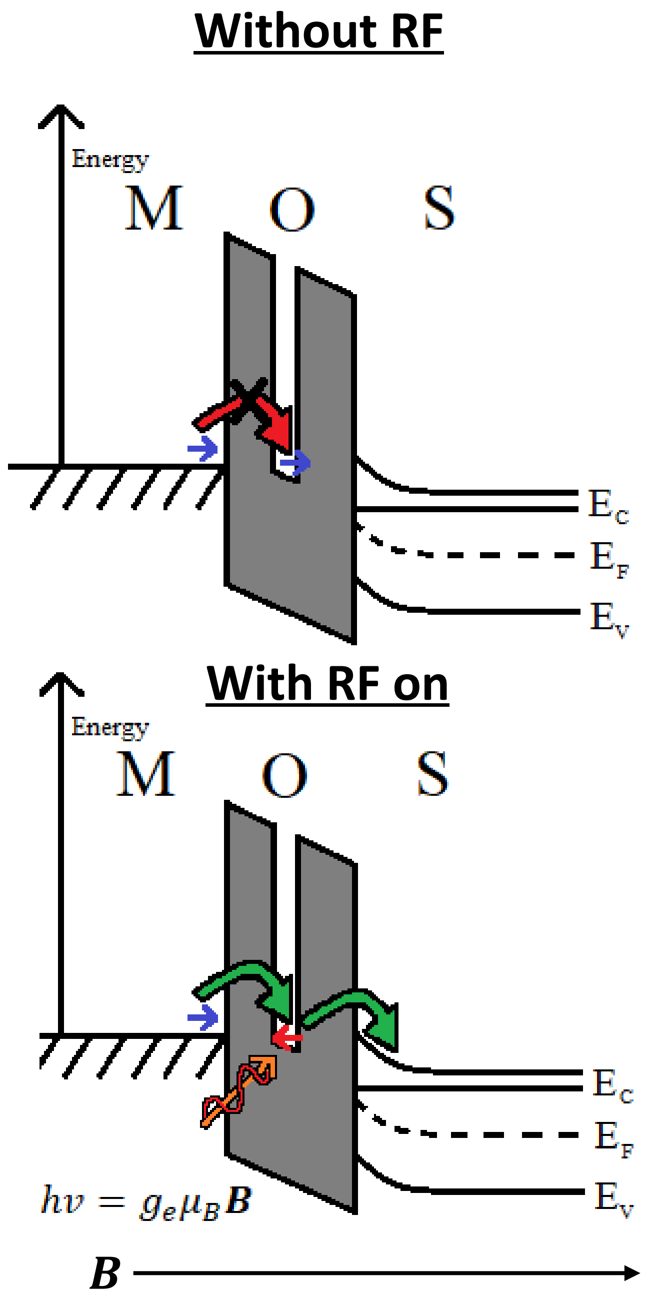
Electrically Detected Magnetic Resonance (EDMR)

- Classical EPR is not sensitive enough to study traps in practical MOSFETs (sensitivity $\cong 10^{10}$ defects).
- EDMR sensitivity is about 10^7 times greater than EPR [1].
- This sensitivity boost makes EDMR an incredibly powerful analytical tool for analyzing the chemical nature of paramagnetic defects in technologically meaningful devices.



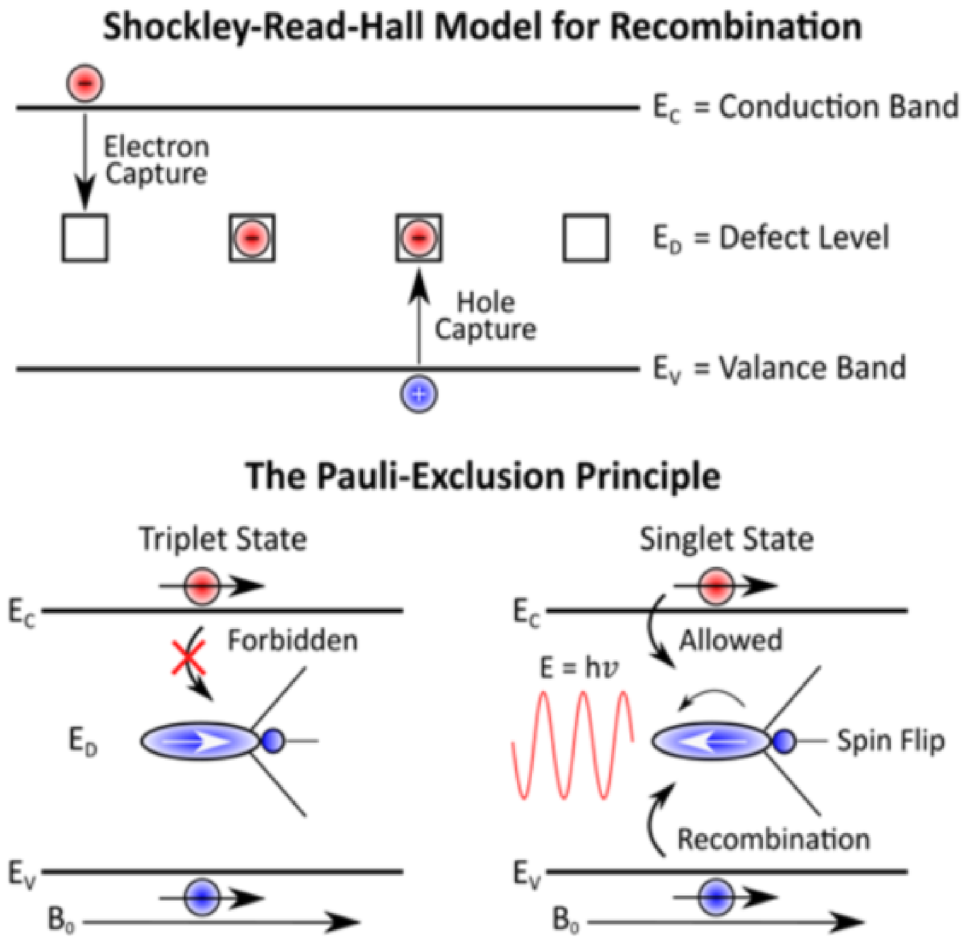
Spin-Dependent Trap Assisted Tunneling (SDTAT)

- Works on the principles of variable range hopping.
  - Trap to trap tunneling events conserve intrinsic angular momentum; they are a function of both energy and tunneling distance.
- RF induced resonance events can "flip" the spins of oxide defects, allowing forbidden tunneling transitions to occur.

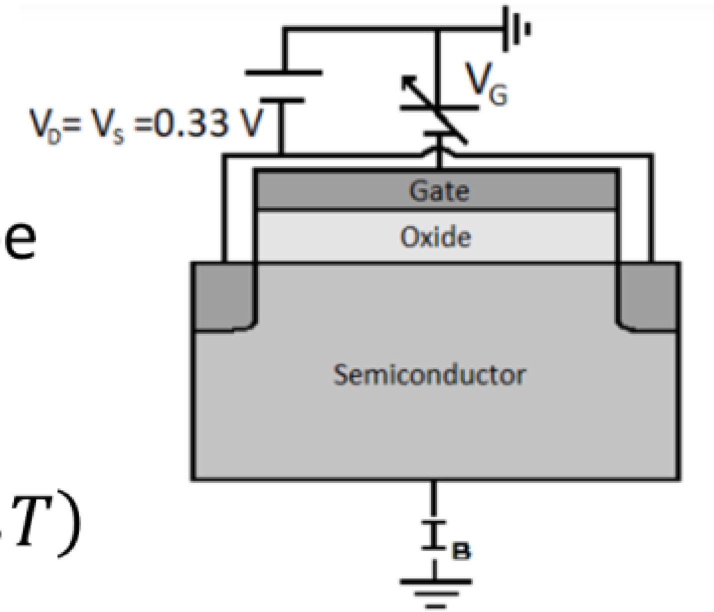


EDMR via Spin-Dependent Recombination (SDR)

- Shockley-Read-Hall Model for Recombination.
- Pauli Exclusion Principle forbids capture if conduction electron/deep level electron have the same spin quantum number.
- Magnetic resonance “flips” the defect electron spin, allowing previously forbidden capture and recombination.
- This increases the recombination current at resonance.



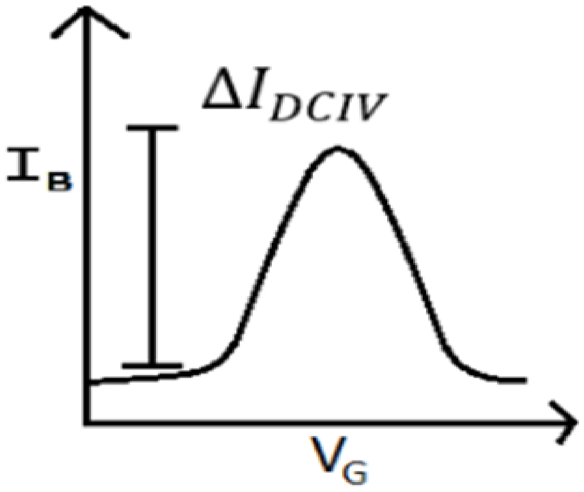
Gated Diode (dc I-V) EDMR



- Developed by Grove and Fitzgerald [2], dc I-V can be used to calculate interface densities using the equation:

$$\Delta I_{DCIV} = \frac{1}{2} q_0 n_i \sigma v_{th} D_{it} A q_0 |V_e| \exp(q_0 |V_e| 2\mathrm{k}_B T)$$

- The dc I-V peak voltage is the biasing condition for EDMR.

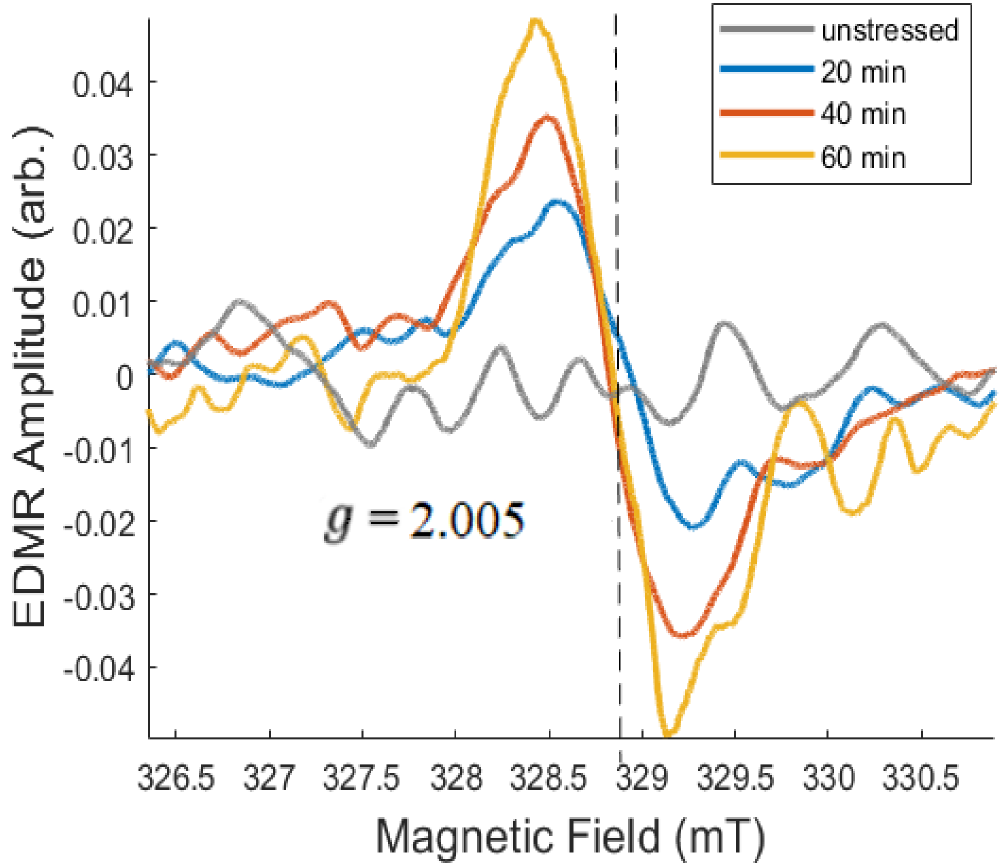


Experimental

- Identical 1.89×10^{-5} cm^2 Si/SiO_2 total gate area nMOSFETS with 7.5 nm thick oxides.
- MOS structures consisting of 126 devices, all with 15 by 1 μm channel dimensions.
- During EDMR, dc I-V source/drain biases used were -0.33 V.
- All high-field stressing was done at a constant gate bias of -9 V for various lengths of time.
- All EDMR measurements were done with the magnetic field perpendicular to the (100) interface plane.

SDTAT Results on High-Field Stressed MOSFETs

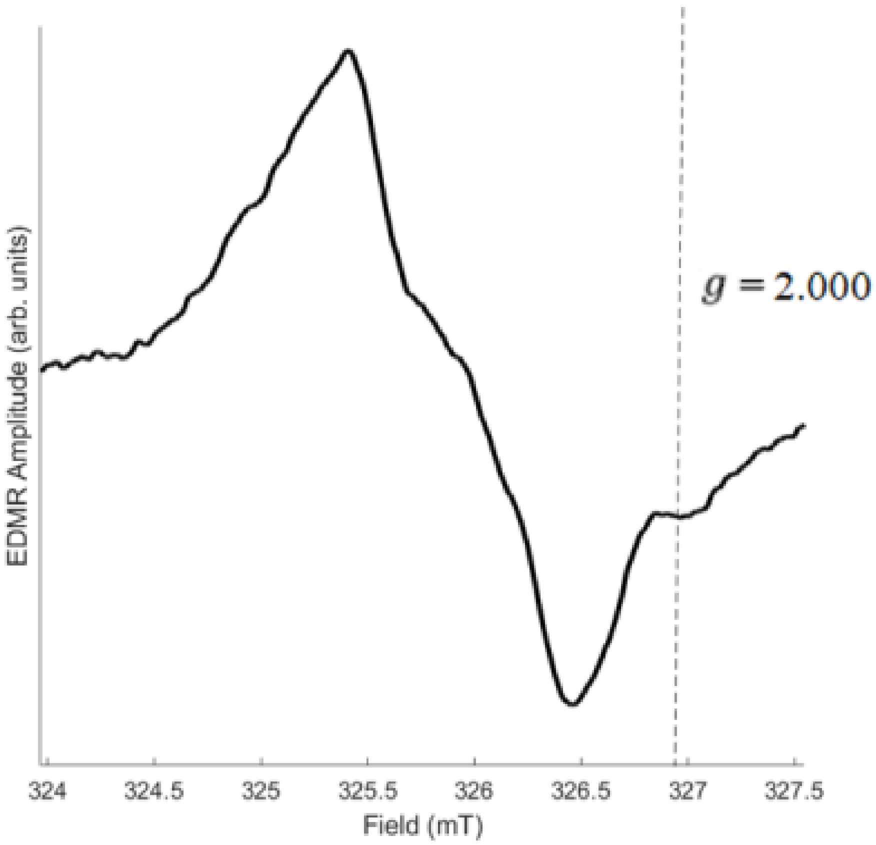
- Signal of SDTAT response increases with high-field stressing time.
- Dominant features were the P_{b0} ($g = 2.0065$) and P_{b1} ($g = 2.0032$) center.
- The EDMR results are in close correspondence with the increase in D_{it} measured via dc I-V.



	Unstressed	20 min	40 min	60 min
Mid-gap D_{it} (10^{11} cm^{-2} eV)	.117	10.934	14.826	18.188

Low-Temperature dc I-V EDMR

- Along with the P_{b0} and P_{b1}, there is an additional feature that forms at $g = 2.000$ with high-field stressing.
- This defect could only be due to an E' center.
- All evidence points to the generation of E' with high-field stressing: So where is the E' in SDTAT?
  - Overwhelmed by the P_b response.
  - Rate-limiting interactions.

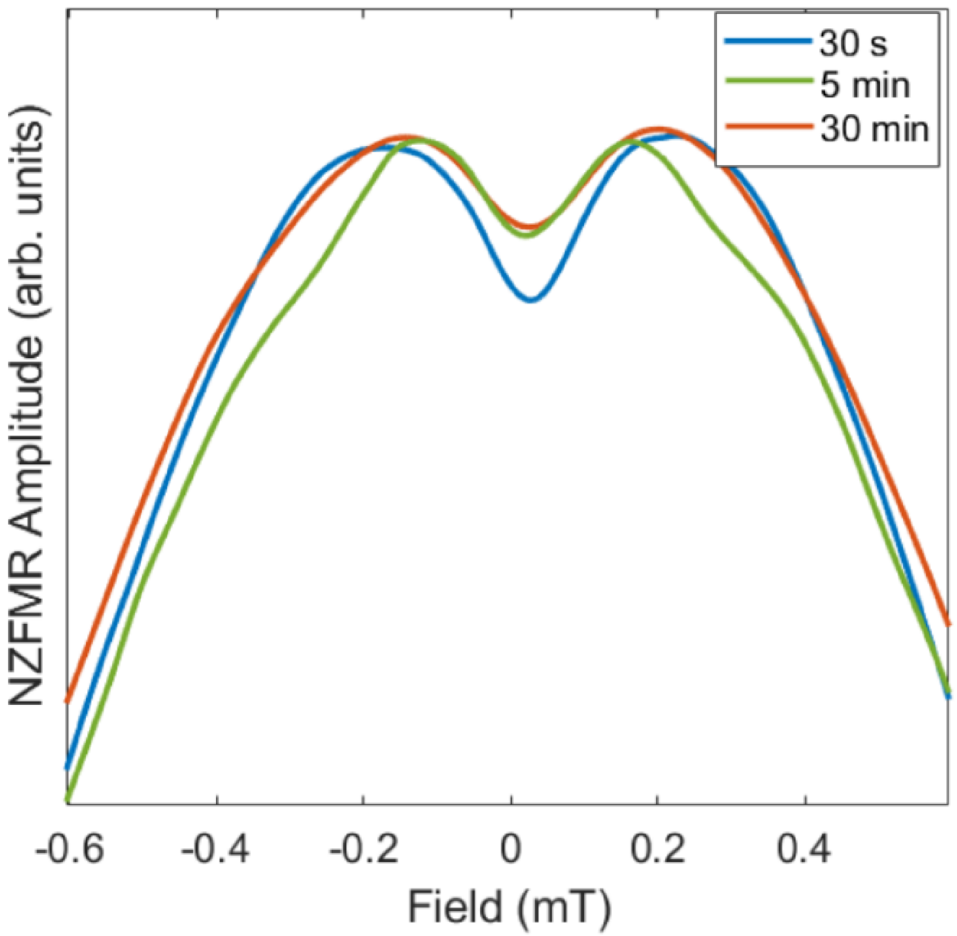


Near-Zero Field Magnetoresistance (NZFMR)

- Can detect both SDTAT and SDR without an RF microwave source.
  - No B_1 is necessary; great potential for analyzing “packaged” devices.
- NZFMR utilizes the mixing of states at near-zero fields due to local magnetic field interactions.
- The theoretical NZFMR response can be modeled via the Stochastic Quantum Liouville Equation (SLE), a theory developed by Flatté and Harmon [3] and advanced for use in MOS devices by Frantz, Harmon, and Flatté [4].

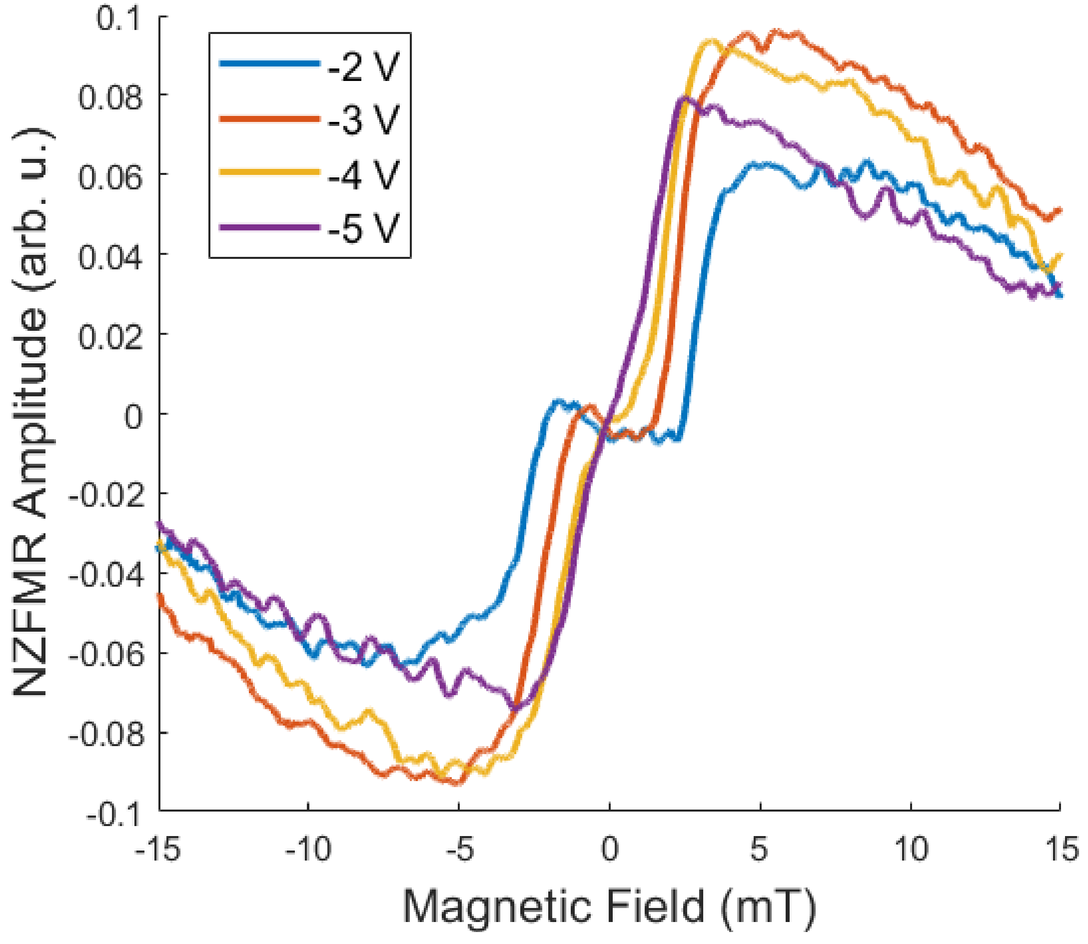
NZMFR via SDR

- Changes in line shape are critical in the analysis of NZFMR spectra.
- These changes can only be due to two factors: kinetics and hyperfine interactions.
- For a constant V_f, the recombination kinetics must be constant.
- Only magnetic nuclei in system are $^{29}\mathrm{Si}$ nuclei (4.7%) and H (100%).
- The results demonstrate that hydrogen is being redistributed throughout high-field stressing.



NZFMR SDTAT: Changes With Bias During NZFMR Measurement

- In this case, NZFMR spectral changes will be due to kinetics.
- The NZFMR spectra show large changes in the unusually large linewidths of the signals.
- This NZFMR technology, paired with modeling via the SLE, could be used as a figure of merit for hopping rates/trap distances for modeling TDDB.



Conclusions

- We provide evidence and chemical identification of both interface (P_{b0} and P_{b1}) traps and oxide (E') defects generated in Si/SiO_2 MOSFETs during the early to middle stages of TDDB.
- We find that the dominant defect in the SDTAT spectrum in these high-field stressed MOSFETs are the P_{b0} and P_{b1} defects.
- We show that the interface-to-oxide tunneling event is the rate-limiting step in Si/SiO_2 in the earlier stages of TDDB.

References

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